

IN THE SPECIFICATION:

Please replace paragraph [0022] with the following amended paragraph:

[0022] In order to perform plasma etching, a substrate, e.g., a glass reticle, is placed within a processing chamber. An example of such a chamber is schematically shown in **Figure 1**. The process chamber **100** of **Figure 1** has a substrate support member **200** disposed therein, and a substrate handler blade **300** positioned adjacent thereto. Substrate[[s]] **222** [[are]] is shown positioned on ~~both the substrate support member **200** and the handler blade **300**.~~

Please replace paragraph [0026] with the following amended paragraph:

[0026] With respect to the substrate support member **200** itself, the support member **200** defines a pedestal for the substrate **222** during processing. The support member **200** first comprises a body **206**. The body **206** has an upper surface that defines a substrate support base **210** (seen in **Figure 2**). In one arrangement, the substrate support base **210** is a separate piece mounted on an upper surface of the body **206**. An optional substrate supporting assembly **215** is preferably provided over the base **210** to aid in transporting the substrate **222** into and out of the chamber **100**. The substrate supporting assembly **215** is shown in detail in **Figure 2**. ~~Only the capture ring **216** of the supporting assembly **215** is seen in **Figure 1**.~~

Please replace paragraph [0032] with the following amended paragraph:

[0032] The capture ring **220** defines an arcuate base plate having an inner diameter **207** and an outer diameter **202**. A central bore **206** is formed within the inner diameter **207** of the capture ring **220**. The diameters **207**, **202** of the capture ring **220** are not continuous, but retain an opening that serves as part of the bore **206**. As with the cover ring **216**, the capture ring **220** includes substrate supports **204**, **205**. The substrate supports **204**, **205** generally follow the inner diameter **207** of the capture ring **220**. In the arrangement of Figure 2, the supports **204**, **205** define shoulders disposed along the inner diameter **207**. The substrate supports **204**, **205** and the ~~base plate **202**~~ inner diameter **207** form a substrate receiving area. The shoulders **204**, **205** and the base

~~plate 202~~ inner diameter 207 are adapted to mate with the substrate supports **218** on the cover ring **216**. When the capture ring **220** is rested upon the cover ring **216**, the substrate supports **205** for the capture ring **220** are co-planar with the substrate supports **218** for the cover ring. The capture ring **220** is dimensioned to rest on the cover ring **216** without covering the two raised surfaces **221**, ~~[[222]]~~ 223 on the cover ring **216**. Together, the substrate supports **205**, **218** may then seamlessly receive a substrate (not shown).

Please replace paragraph [0041] with the following amended paragraph:

[0041] The dielectric material portion **318** of the body **306** may be of different thicknesses. This is demonstrated in the schematic embodiments shown in **Figures 4** and **5**. **Figure 4** provides a cross-sectional view of a pedestal **300'** of the present invention. The pedestal **300'** is shown schematically. Likewise, **Figure 5** presents a cross-sectional view of a pedestal ~~[[300']]~~ 300'' of the present invention, in an alternate embodiment. The pedestal **300''** is again shown schematically. In each view, a reticle **222** is shown being supported on the respective pedestal **300'**, **300''**. Further, in each view a cover **315** is provided. The cover **315** may be configured in accordance with the cover **215** shown in the exploded view of **Figure 2**. The cover **315** is preferably fabricated from a dielectric material. The use of different dielectric material thickness is to adjust or control the relative RF power coupled to the reticle. One benefit of using a dielectric material is it enables the use of two control knobs, that is knobs for dielectric constant and thickness. This, in turn, enables the operator to change the relative amounts of RF that goes into the reticle versus the RF power that goes to the pedestal area surrounding the reticle. The dielectric thickness and type may be such that the relative amount is the same for uniform power distribution, or different if needed for compensating for the etch process.